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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	667MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8349evvalfb

- Complies with USB specification Rev. 2.0
- Can operate as a stand-alone USB device
  - One upstream facing port
  - Six programmable USB endpoints
- Can operate as a stand-alone USB host controller
  - USB root hub with one downstream-facing port
  - Enhanced host controller interface (EHCI) compatible
  - High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
- External PHY with UTMI, serial and UTMI+ low-pin interface (ULPI)

• Universal serial bus (USB) multi-port host controller
- Can operate as a stand-alone USB host controller
  - USB root hub with one or two downstream-facing ports
  - Enhanced host controller interface (EHCI) compatible
  - Complies with *USB Specification Rev. 2.0*
- High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
- Direct connection to a high-speed device without an external hub
- External PHY with serial and low-pin count (ULPI) interfaces

• Local bus controller (LBC)
- Multiplexed 32-bit address and data operating at up to 133 MHz
- Eight chip selects for eight external slaves
- Up to eight-beat burst transfers
- 32-, 16-, and 8-bit port sizes controlled by an on-chip memory controller
- Three protocol engines on a per chip select basis:
  - General-purpose chip select machine (GPCM)
  - Three user-programmable machines (UPMs)
  - Dedicated single data rate SDRAM controller
- Parity support
- Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)

• Programmable interrupt controller (PIC)
- Functional and programming compatibility with the MPC8260 interrupt controller
- Support for 8 external and 35 internal discrete interrupt sources
- Support for 1 external (optional) and 7 internal machine checkstop interrupt sources
- Programmable highest priority request
- Four groups of interrupts with programmable priority
- External and internal interrupts directed to host processor
- Redirects interrupts to external $\overline{\text{INTA}}$ pin in core disable mode.
- Unique vector number for each interrupt source

- Dual industry-standard I^{2}C interfaces
  - Two-wire interface
  - Multiple master support
  - Master or slave I^{2}C mode support
  - On-chip digital filtering rejects spikes on the bus
  - System initialization data optionally loaded from I^{2}C-1 EPROM by boot sequencer embedded hardware
- DMA controller
  - Four independent virtual channels
  - Concurrent execution across multiple channels with programmable bandwidth control
  - Handshaking (external control) signals for all channels: $\overline{\text{DMA\_DREQ}}$[0:3], $\overline{\text{DMA\_DACK}}$[0:3], $\overline{\text{DMA\_DDONE}}$[0:3]
  - All channels accessible to local core and remote PCI masters
  - Misaligned transfer capability
  - Data chaining and direct mode
  - Interrupt on completed segment and chain
- DUART
  - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Serial peripheral interface (SPI) for master or slave
- General-purpose parallel I/O (GPIO)
  - 64 parallel I/O pins multiplexed on various chip interfaces
- System timers
  - Periodic interrupt timer
  - Real-time clock
  - Software watchdog timer
  - Eight general-purpose timers
- Designed to comply with IEEE Std. 1149.1™, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8349EA. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2 Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
3 Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.
4 Maximum power is based on a voltage of V_{DD} = 1.2 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.
5 Typical power is based on a voltage of V_{DD} = 1.3 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
6 Maximum power is based on a voltage of V_{DD} = 1.3 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.

Table 5 shows the estimated typical I/O power dissipation for MPC8349EA.

Table 5. MPC8349EA Typical I/O Power Dissipation

Interface	Parameter	GV_{DD} (1.8 V)	GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V Rs = 20 Ω Rt = 50 Ω 2 pair of clocks	200 MHz, 32 bits	0.31	0.42	—	—	—	W	—
	200 MHz, 64 bits	0.42	0.55	—	—	—	W	—
	266 MHz, 32 bits	0.35	0.5	—	—	—	W	—
	266 MHz, 64 bits	0.47	0.66	—	—	—	W	—
	300 MHz, 32 bits	0.37	0.54	—	—	—	W	—
	300 MHz, 64 bits	0.50	0.7	—	—	—	W	—
	333 MHz, 32 bits	0.39	0.58	—	—	—	W	—
	333 MHz, 64 bits	0.53	0.76	—	—	—	W	—
	400 MHz, 32 bits	0.44	—	—	—	—	—	—
	400 MHz, 64 bits	0.59	—	—	—	—	—	—
PCI I/O load = 30 pF	33 MHz, 64 bits	—	—	0.08	—	—	W	—
	66 MHz, 64 bits	—	—	0.14	—	—	W	—
	33 MHz, 32 bits	—	—	0.04	—	—	W	Multiply by 2 if using 2 ports.
	66 MHz, 32 bits	—	—	0.07	—	—	W	
Local bus I/O load = 25 pF	133 MHz, 32 bits	—	—	0.27	—	—	W	—
	83 MHz, 32 bits	—	—	0.17	—	—	W	—
	66 MHz, 32 bits	—	—	0.14	—	—	W	—
	50 MHz, 32 bits	—	—	0.11	—	—	W	—
TSEC I/O load = 25 pF	MII	—	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	—	0.06	—	W	
	RGMII or RTBI	—	—	—	—	0.04	W	
USB	12 MHz	—	—	0.01	—	—	W	Multiply by 2 if using 2 ports.
	480 MHz	—	—	0.2	—	—	W	
Other I/O	—	—	—	0.01	—	—	W	—

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the device.

4.1 DC Electrical Characteristics

Table 6 provides the clock input (CLKIN/PCI_SYNC_IN) DC timing specifications for the MPC8349EA.

Table 6. CLKIN DC Timing Specifications

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.7	OV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.4	V
CLKIN input current	$0\ V \le V_{IN} \le OV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	$0\ V \le V_{IN} \le 0.5\ V$ or $OV_{DD} - 0.5\ V \le V_{IN} \le OV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	$0.5\ V \le V_{IN} \le OV_{DD} - 0.5\ V$	I_{IN}	—	±50	μA

4.2 AC Electrical Characteristics

The primary clock source for the MPC8349EA can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 7 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the device.

Table 7. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	—	—	66	MHz	1, 6
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN/PCI_CLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	2.3	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The system, core, USB, security, and TSEC must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be < 500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.
6. Spread spectrum clocking is allowed with 1% input frequency down-spread at maximum 50 KHz modulation rate regardless of input frequency.

4.3 TSEC Gigabit Reference Clock Timing

Table 8 provides the TSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications.

Table 8. EC_GTX_CLK125 AC Timing Specifications

At recommended operating conditions with LV_{DD} = 2.5 ± 0.125 mV/ 3.3 V ± 165 mV

Parameter	Symbol	Min	Typical	Max	Unit	Notes
EC_GTX_CLK125 frequency	t_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK125 rise and fall time LV_{DD} = 2.5 V LV_{DD} = 3.3 V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2
EC_GTX_CLK125 jitter	—	—	—	±150	ps	2

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5 and 2.0 V for LV_{DD} = 2.5 V and from 0.6 and 2.7 V for LV_{DD} = 3.3 V.
2. EC_GTX_CLK125 is used to generate the GTX clock for the eTSEC transmitter with 2% degradation. The EC_GTX_CLK125 duty cycle can be loosened from 47%/53% as long as the PHY device can tolerate the duty cycle generated by the eTSEC GTX_CLK. See Section 8.2.4, "RGMII and RTBI AC Timing Specifications for the duty cycle for 10Base-T and 100Base-T reference clock.

5 RESET Initialization

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8349EA.

5.1 RESET DC Electrical Characteristics

Table 9 provides the DC electrical characteristics for the RESET pins of the MPC8349EA.

Table 9. RESET Pins DC Electrical Characteristics[1]

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage[2]	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V

8.1.1 TSEC DC Electrical Characteristics

GMII, MII, TBI, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 23 and Table 24. The RGMII and RTBI signals in Table 24 are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 23. GMII/TBI and MII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD}[2]	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	LV_{DD} = Min	2.40	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	40	μA
Input low current	I_{IL}	V_{IN}[1] = GND		–600	—	μA

Notes:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.
2. GMII/MII pins not needed for RGMII or RTBI operation are powered by the OV_{DD} supply.

Table 24. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	10	μA
Input low current	I_{IL}	V_{IN}[1] = GND		–15	—	μA

Note:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2 GMII, MII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

Table 26. GMII Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock rise (20%–80%)	t_{GRXR}	—	—	1.0	ns
RX_CLK clock fall time (80%–20%)	t_{GRXF}	—	—	1.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 10 shows the GMII receive AC timing diagram.

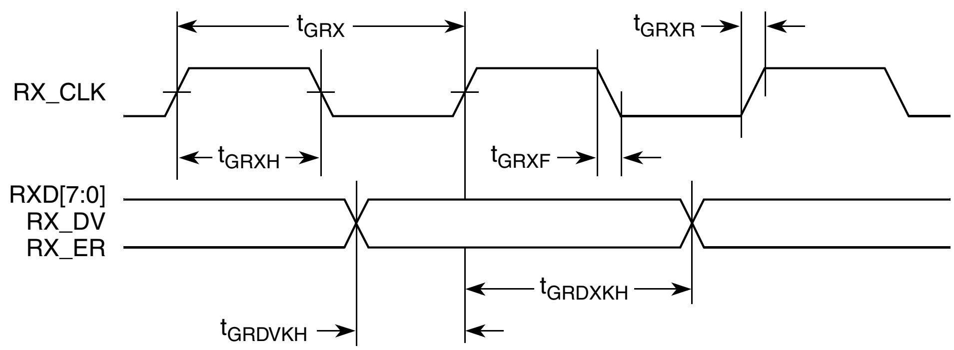


Figure 10. GMII Receive AC Timing Diagram

8.2.2 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.2.1 MII Transmit AC Timing Specifications

Table 27 provides the MII transmit AC timing specifications.

Table 27. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns

Table 27. MII Transmit AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK data clock rise (20%–80%)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall (80%–20%)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). In general, the clock reference symbol is based on two to three letters representing the clock of a particular function. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 11 shows the MII transmit AC timing diagram.

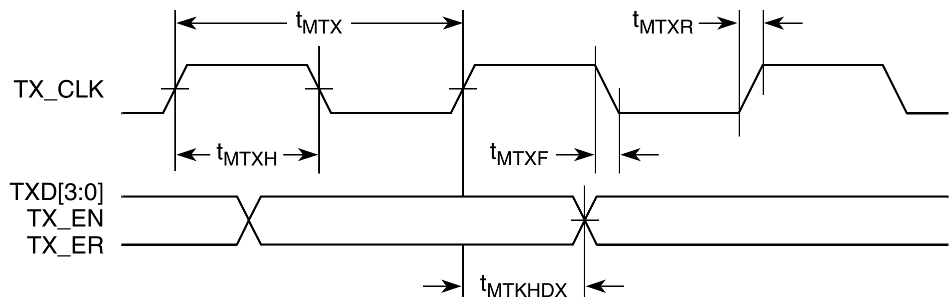


Figure 11. MII Transmit AC Timing Diagram

8.2.2.2 MII Receive AC Timing Specifications

Table 28 provides the MII receive AC timing specifications.

Table 28. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns

Table 32. MII Management DC Electrical Characteristics Powered at 2.5 V (continued)

Parameter	Symbol	Conditions	Min	Max	Unit
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}	—	10	μA
Input low current	I_{IL}	$V_{IN} = LV_{DD}$	–15	—	μA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

Table 33. MII Management DC Electrical Characteristics Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	LV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.10	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input high current	I_{IH}	LV_{DD} = Max	V_{IN}[1] = 2.1 V	—	40	μA
Input low current	I_{IL}	LV_{DD} = Max	V_{IN} = 0.5 V	–600	—	μA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.3.2 MII Management AC Electrical Specifications

Table 34 provides the MII management AC timing specifications.

Table 34. MII Management AC Timing Specifications

At recommended operating conditions with LV_{DD} is 3.3 V ± 10% or 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	3
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—

9 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8349EA.

9.1 USB DC Electrical Characteristics

Table 35 provides the DC electrical characteristics for the USB interface.

Table 35. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current	I_{IN}	—	±5	μA
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

9.2 USB AC Electrical Specifications

Table 36 describes the general timing parameters of the USB interface of the MPC8349EA.

Table 36. USB General Timing Parameters (ULPI Mode Only)

Parameter	Symbol[1]	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	15	—	ns	2–5
Input setup to USB clock—all inputs	t_{USIVKH}	4	—	ns	2–5
Input hold to USB clock—all inputs	t_{USIXKH}	1	—	ns	2–5
USB clock to output valid—all outputs	t_{USKHOV}	—	7	ns	2–5
Output hold from USB clock—all outputs	t_{USKHOX}	2	—	ns	2–5

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{USIXKH} symbolizes USB timing (US) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to USB clock.
3. All signals are measured from OV_{DD}/2 of the rising edge of the USB clock to 0.4 × OV_{DD} of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

10.2 Local Bus AC Electrical Specification

Table 38 and Table 39 describe the general timing parameters of the local bus interface of the MPC8349EA.

Table 38. Local Bus General Timing Parameters—DLL On

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	1.5	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	2.2	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
LUPWAIT Input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to LALE rise	t_{LBKHLR}	—	4.5	ns	—
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	4.5	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	4.5	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	4.5	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	1	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	1	—	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	3.8	ns	8

Notes:
1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to the rising edge of LSYNC_IN.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin equals the load on the LAD output pins.
8. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

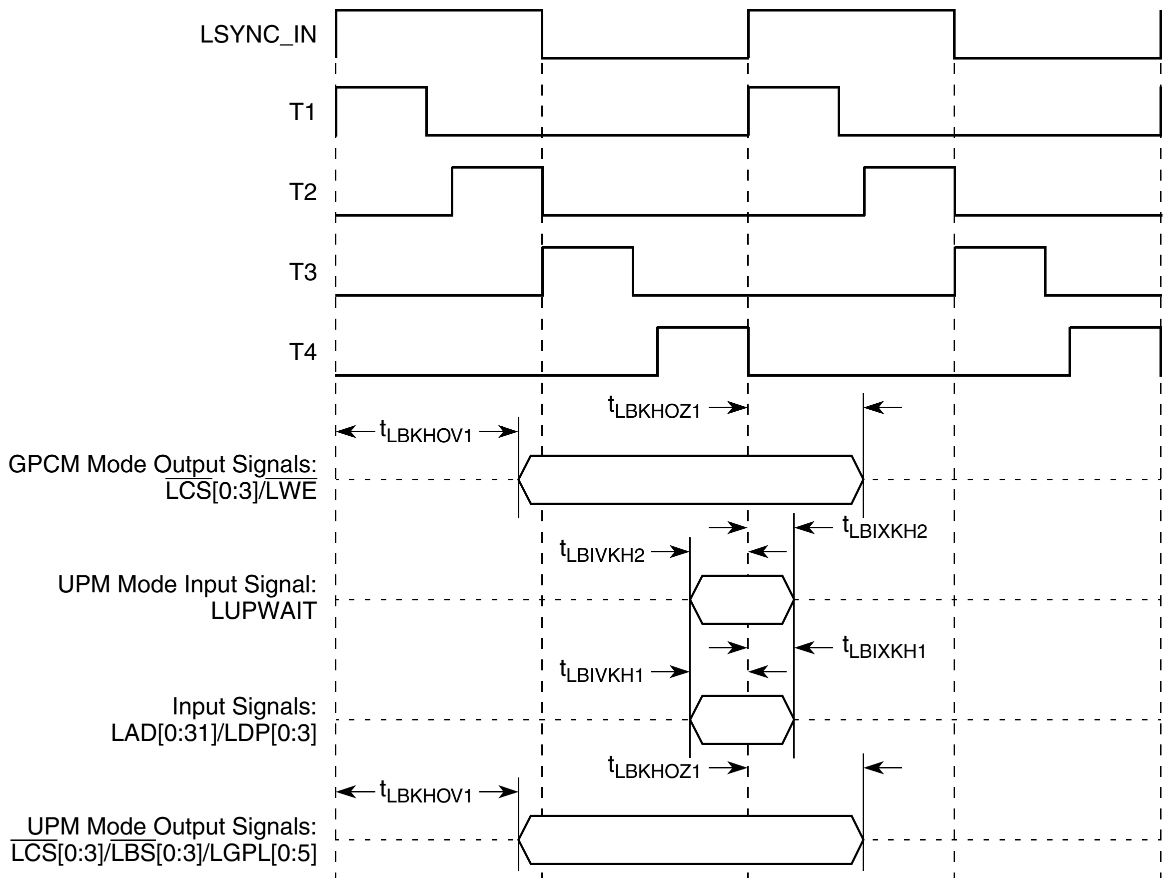


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Enabled)

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA.

11.1 JTAG DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA.

Table 40. JTAG Interface DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	OV_{DD} – 0.3	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V

Figure 30 provides the boundary-scan timing diagram.

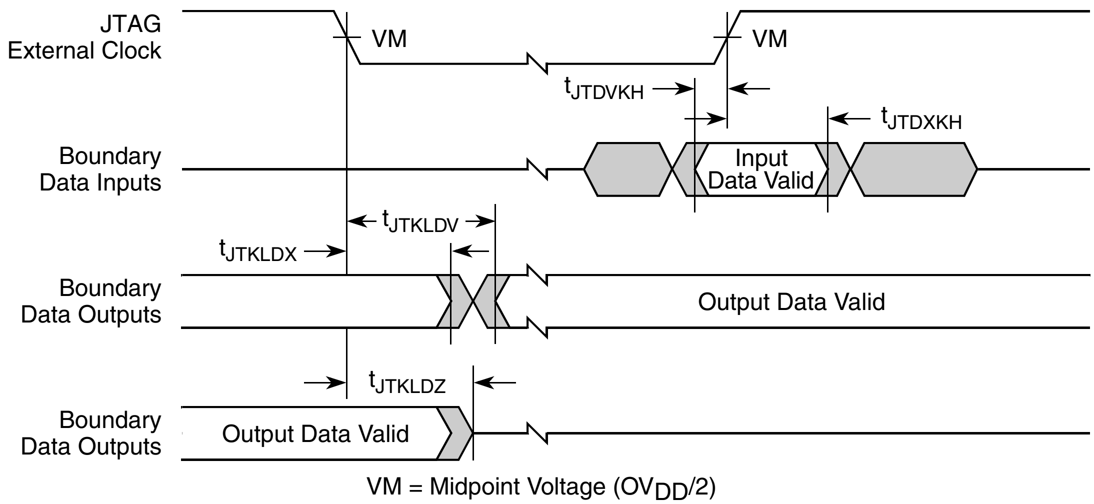


Figure 30. Boundary-Scan Timing Diagram

Figure 31 provides the test access port timing diagram.

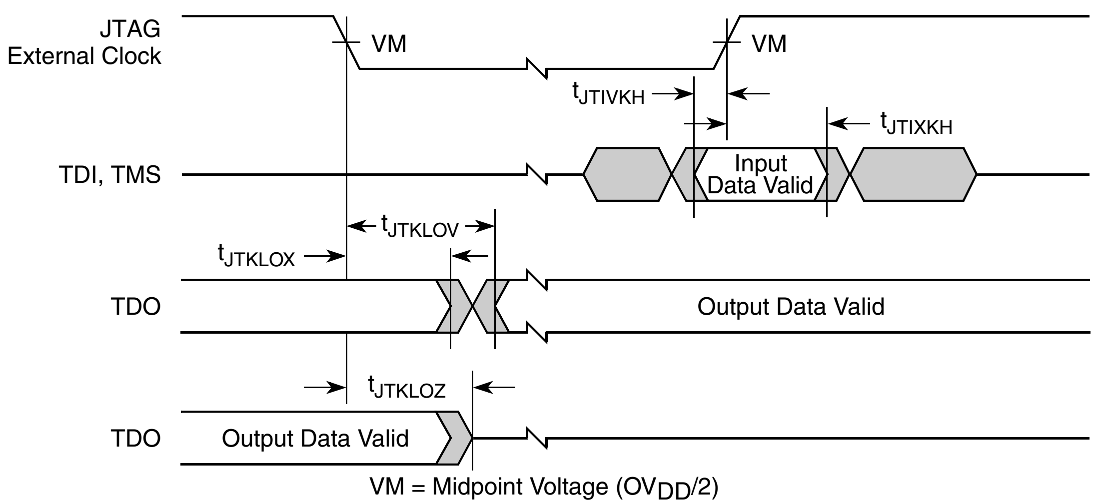


Figure 31. Test Access Port Timing Diagram

12 I^2C

This section describes the DC and AC electrical characteristics for the I^2C interface of the MPC8349EA.

12.1 I^2C DC Electrical Characteristics

Table 42 provides the DC electrical characteristics for the I^2C interface of the MPC8349EA.

Table 42. I^2C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	4
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:
1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8349EA Integrated Host Processor Family Reference Manual,* for information on the digital filter used.
4. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

12.2 I^2C AC Electrical Specifications

Table 43 provides the AC timing parameters for the I^2C interface of the MPC8349EA. Note that all values refer to V_{IH}(min) and V_{IL}(max) levels (see Table 42).

Table 43. I^2C AC Electrical Specifications

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	μs
High period of the SCL clock	t_{I2CH}	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs
Data setup time	t_{I2DVKH}	100	—	ns
Data hold time:CBUS compatible masters I^2C bus devices	t_{I2DXKL}	— 0[2]	— 0.9[3]	μs

Table 45. PCI AC Timing Specifications at 66 MHz[1] (continued)

Parameter	Symbol[2]	Min	Max	Unit	Notes
$\overline{\text{PORESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	6

Notes:
1. PCI timing depends on M66EN and the ratio between PCI1/PCI2. Refer to the PCI chapter of the reference manual for a description of M66EN.
2. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
3. See the timing measurement conditions in the *PCI 2.3 Local Bus Specifications*.
4. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Input timings are measured at the pin.
6. The setup and hold time is with respect to the rising edge of $\overline{\text{PORESET}}$.

Table 46 provides the PCI AC timing specifications at 33 MHz.

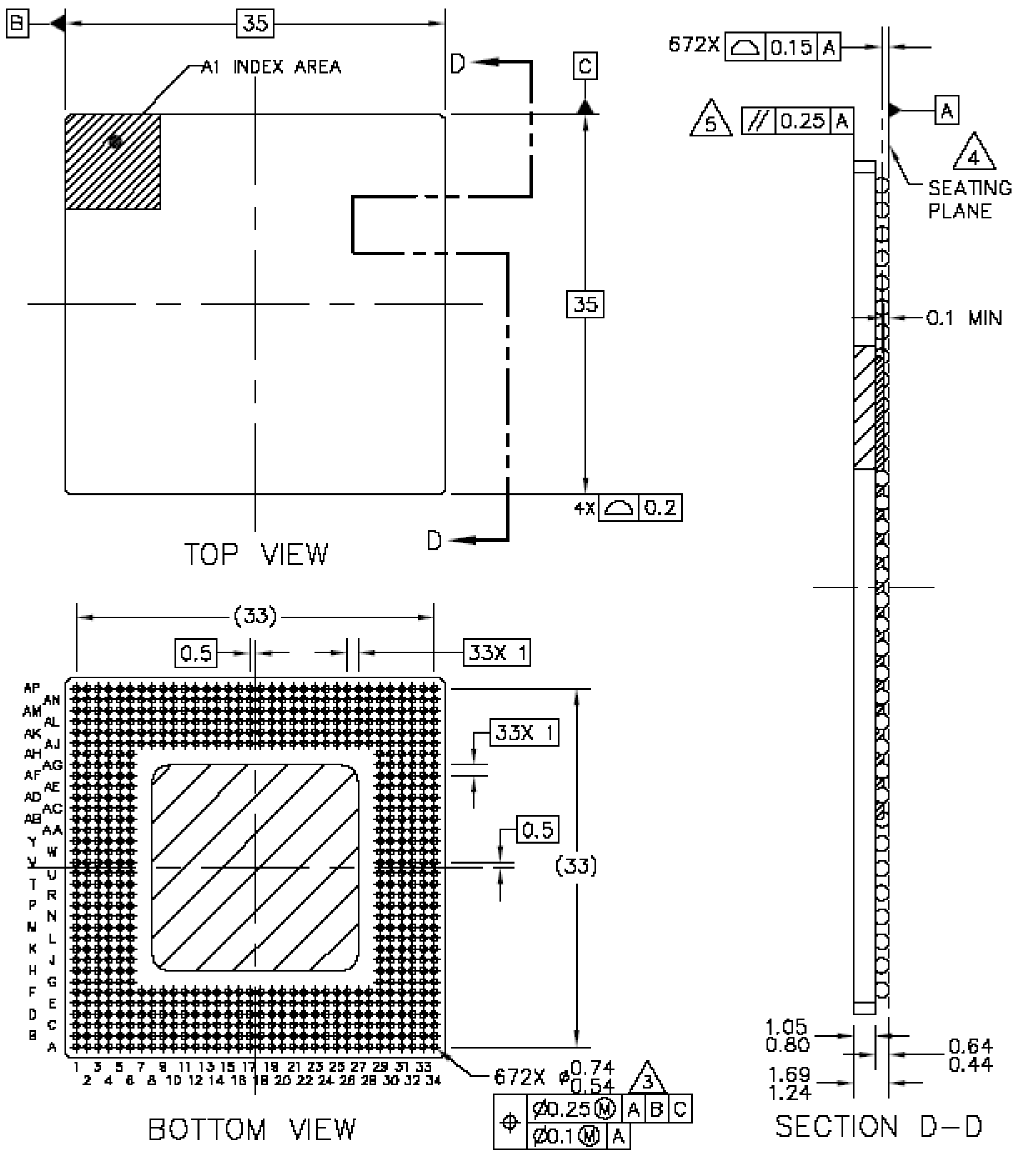
Table 46. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	11	ns	2
Output hold from clock	t_{PCKHOX}	2	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0	—	ns	2, 4
$\overline{\text{REQ64}}$ to $\overline{\text{PORESET}}$ setup time	t_{PCRVRH}	5	—	clocks	5
$\overline{\text{PORESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	5

Notes:
1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.3 Local Bus Specifications*.
3. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.
5. The setup and hold time is with respect to the rising edge of $\overline{\text{PORESET}}$.

18.2 Mechanical Dimensions for the MPC8349EA TBGA

Figure 40 shows the mechanical dimensions and bottom surface nomenclature for the MPC8349EA, 672-TBGA package.



Notes:
1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
5. Parallelism measurement must exclude any effect of mark on top surface of package.

Figure 40. Mechanical Dimensions and Bottom Surface Nomenclature for the MPC8349EA TBGA

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO1[2]/DMA_DDONE0/ GTM1_TOUT1	B25	I/O	OV_{DD}	—
GPIO1[3]/DMA_DREQ1/GTM1_TIN2/ GTM2_TIN1	D24	**I/O**	OV_{DD}	—
GPIO1[4]/DMA_DACK1/ GTM1_TGATE2/GTM2_TGATE1	A25	**I/O**	OV_{DD}	—
GPIO1[5]/DMA_DDONE1/ GTM1_TOUT2/GTM2_TOUT1	B24	**I/O**	OV_{DD}	—
GPIO1[6]/DMA_DREQ2/GTM1_TIN3/ GTM2_TIN4	A24	**I/O**	OV_{DD}	—
GPIO1[7]/DMA_DACK2/ GTM1_TGATE3/GTM2_TGATE4	D23	**I/O**	OV_{DD}	—
GPIO1[8]/DMA_DDONE2/ GTM1_TOUT3	B23	**I/O**	OV_{DD}	—
GPIO1[9]/DMA_DREQ3/GTM1_TIN4/ GTM2_TIN3	A23	**I/O**	OV_{DD}	—
GPIO1[10]/DMA_DACK3/ GTM1_TGATE4/GTM2_TGATE3	F22	**I/O**	OV_{DD}	—
GPIO1[11]/DMA_DDONE3/ GTM1_TOUT4/GTM2_TOUT3	E22	**I/O**	OV_{DD}	—
USB Port 1				
MPH1_D0_ENABLEN/ DR_D0_ENABLEN	A26	I/O	OV_{DD}	—
MPH1_D1_SER_TXD/ DR_D1_SER_TXD	B26	I/O	OV_{DD}	—
MPH1_D2_VMO_SE0/ DR_D2_VMO_SE0	D25	I/O	OV_{DD}	—
MPH1_D3_SPEED/DR_D3_SPEED	A27	I/O	OV_{DD}	—
MPH1_D4_DP/DR_D4_DP	B27	I/O	OV_{DD}	—
MPH1_D5_DM/DR_D5_DM	C27	I/O	OV_{DD}	—
MPH1_D6_SER_RCV/ DR_D6_SER_RCV	D26	I/O	OV_{DD}	—
MPH1_D7_DRVVBUS/ DR_D7_DRVVBUS	E26	I/O	OV_{DD}	—
MPH1_NXT/DR_SESS_VLD_NXT	D27	I	OV_{DD}	—
MPH1_DIR_DPPULLUP/ DR_XCVR_SEL_DPPULLUP	A28	I/O	OV_{DD}	—
MPH1_STP_SUSPEND/ DR_STP_SUSPEND	F26	O	OV_{DD}	—

As shown in Figure 41, the primary clock input (frequency) is multiplied up by the system phase-locked loop (PLL) and the clock unit to create the coherent system bus clock (*csb_clk*), the internal clock for the DDR controller (*ddr_clk*), and the internal clock for the local bus interface unit (*lbiu_clk*).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

csb_clk = {PCI_SYNC_IN × (1 + CFG_CLKIN_DIV)} × SPMF

In PCI host mode, PCI_SYNC_IN × (1 + CFG_CLKIN_DIV) is the CLKIN frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL), which is loaded at power-on reset or by one of the hard-coded reset options. See the chapter on reset, clocking, and initialization in the *MPC8349EA Reference Manual* for more information on the clock subsystem.

The internal *ddr_clk* frequency is determined by the following equation:

ddr_clk = *csb_clk* × (1 + RCWL[DDRCM])

ddr_clk is not the external memory bus frequency; *ddr_clk* passes through the DDR clock divider (÷2) to create the differential DDR memory bus clock outputs (MCK and $\overline{\text{MCK}}$). However, the data rate is the same frequency as *ddr_clk*.

The internal *lbiu_clk* frequency is determined by the following equation:

lbiu_clk = *csb_clk* × (1 + RCWL[LBIUCM])

lbiu_clk is not the external local bus frequency; *lbiu_clk* passes through the LBIU clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LBIU clock divider ratio is controlled by LCCR[CLKDIV].

In addition, some of the internal units may have to be shut off or operate at lower frequency than the *csb_clk* frequency. Those units have a default clock ratio that can be configured by a memory-mapped register after the device exits reset. Table 56 specifies which units have a configurable clock frequency.

Table 56. Configurable Clock Units

Unit	Default Frequency	Options
TSEC1	*csb_clk/3*	Off, *csb_clk, csb_clk/2, csb_clk/3*
TSEC2, I^{2}C1	*csb_clk/3*	Off, *csb_clk, csb_clk/2, csb_clk/3*
Security core	*csb_clk/3*	Off, *csb_clk,* csb_clk/2, *csb_clk/3*
USB DR, USB MPH	*csb_clk/3*	Off, csb_clk, csb_clk/2, *csb_clk/3*
PCI1, PCI2 and DMA complex	*csb_clk*	Off, *csb_clk*

2. The e300 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in Section 19.2, "Core PLL Configuration."

21.2 PLL Power Supply Filtering

Each PLL gets power through independent power supply pins ($AV_{DD}1$, $AV_{DD}2$, respectively). The AV_{DD} level should always equal to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme.

There are a number of ways to provide power reliably to the PLLs, but the recommended solution is to provide four independent filter circuits as illustrated in Figure 42, one to each of the four AV_{DD} pins. Independent filters to each PLL reduce the opportunity to cause noise injection from one PLL to the other.

The circuit filters noise in the PLL resonant frequency range from 500 kHz to 10 MHz. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

To minimize noise coupled from nearby circuits, each circuit should be placed as closely as possible to the specific AV_{DD} pin being supplied. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

Figure 42 shows the PLL power supply filter circuit.

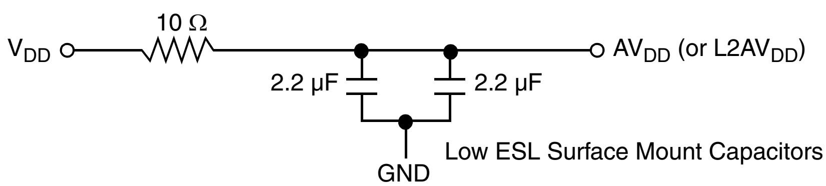


Figure 42. PLL Power Supply Filter Circuit

21.3 Decoupling Recommendations

Due to large address and data buses and high operating frequencies, the MPC8349EA can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8349EA system, and the device itself requires a clean, tightly regulated source of power. Therefore, the system designer should place at least one decoupling capacitor at each V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pin of the device. These capacitors should receive their power from separate V_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND power planes in the PCB, with short traces to minimize inductance. Capacitors can be placed directly under the device using a standard escape pattern. Others can surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, distribute several bulk storage capacitors around the PCB, feeding the V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors are 100–330 µF (AVX TPS tantalum or Sanyo OSCON).

21.4 Connection Recommendations

To ensure reliable operation, connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD}, GV_{DD}, or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD}, GV_{DD}, LV_{DD}, OV_{DD}, and GND pins of the MPC8349EA.

21.5 Output Buffer DC Impedance

The MPC8349EA drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 43). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N) \div 2$.

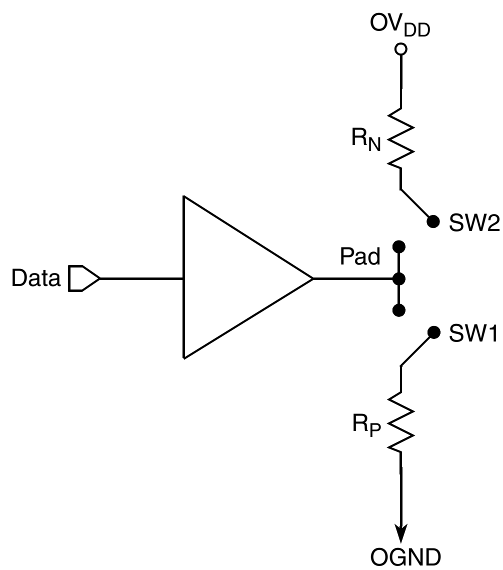


Figure 43. Driver Impedance Measurement

Two measurements give the value of this resistance and the strength of the driver current source. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term}. The measured voltage is